

# **Nucleation and Growth Behavior of Chemically Vapor Deposited Alpha-Al<sub>2</sub>O<sub>3</sub> on Single Crystal Ni-based Superalloy Surface**

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Alpha-Al<sub>2</sub>O<sub>3</sub> is one of the most stable materials in high-temperature combustion environments. However, it is also known that alpha-Al<sub>2</sub>O<sub>3</sub> is one of the most difficult materials to prepare in the form of thin-film. We have developed a novel procedure for preparing a high-quality alpha-Al<sub>2</sub>O<sub>3</sub> coating layer directly on the surface of a single crystal Ni-based superalloy by chemical vapor deposition (CVD). The key feature of this procedure was to pretreat the alloy surface with a CO<sub>2</sub>+H<sub>2</sub> mixture at 1050° C for 1 min prior to a CVD step with AlCl<sub>3</sub>, CO<sub>2</sub>, and H<sub>2</sub> precursors for 10 min at 1050°C in the same reactor chamber. Characterization results showed that the pretreatment step resulted in the formation of a continuous oxide layer (~50 nm) on the alloy surface which consisted of alpha-Al<sub>2</sub>O<sub>3</sub> as the major phase along with a trace amount of theta-Al<sub>2</sub>O<sub>3</sub>. The subsequent CVD-Al<sub>2</sub>O<sub>3</sub> layer was 150 nm thick, and consisted of small columnar grains (~100 to 200 nm) with alpha-Al<sub>2</sub>O<sub>3</sub> as the major phase with a minute amount of theta-Al<sub>2</sub>O<sub>3</sub>. It appeared that the preferential nucleation of alpha-Al<sub>2</sub>O<sub>3</sub> in the pre-oxidized layer was promoted by: (1) rapid heating of the alloy surface to the temperature region, where alpha-Al<sub>2</sub>O<sub>3</sub> was expected to nucleate and (2) the low oxygen pressure environment of the pre-oxidation step which kept the rate of oxidation low.